TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS097

CD40106B Types

CMOS Hex Schmitt Triggers

High-Voltage Types (20-Volt Rating)

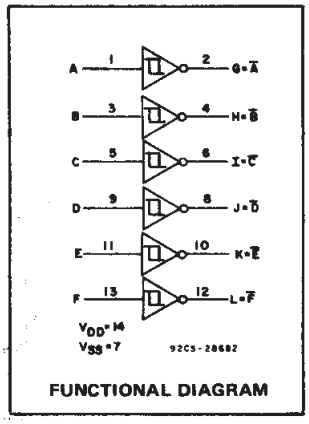
■ CD40106B consists of six Schmitt-trigger circuits. Each circuit functions as an inverter with Schmitt-trigger action on the input. The trigger switches at different points for positive- and negative-going signals. The difference between the positive-going voltage (V_P) and the negative-going voltage (V_N) is defined as hysteresis voltage (V_H) (see Fig.6). The CD40106B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic package (E suffix), and in chip form (H suffix).

Features:

- Schmitt-trigger action with no external components
- Hysteresis voltage (typ.) 0.9 V at V_{DD} = 5 V, 2.3 V at V_{DD} = 10 V, and 3.5 V at V_{DD} = 15 V
- Noise immunity greater than 50%
- No limit on input rise and fall times
- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Low V_{DD} to V_{SS} current during slow input ramp
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Wave and pulse shapers
- High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators



FUNCTIONAL DIAGRAM

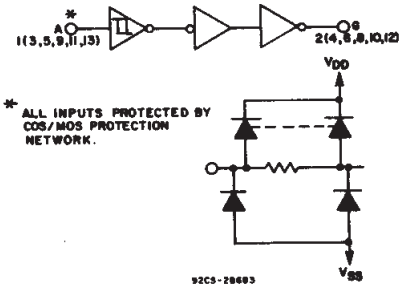


Fig.1 – Logic diagram (1 of 6 Schmitt triggers).

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)..... 100mW
OPERATING-TEMPERATURE RANGE (T_A) .....-55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) .....-65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

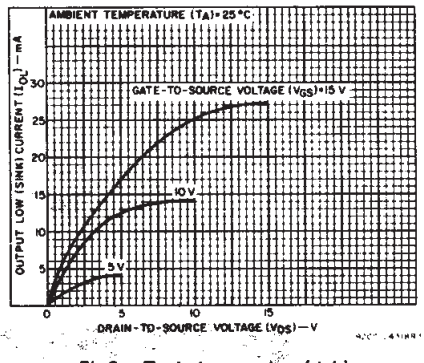


Fig.2 – Typical output low (sink) current characteristics.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A Full Package-Temperature Range)	3	18	V

DYNAMIC ELECTRICAL CHARACTERISTICS

At T_A = 25°C, Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 kΩ

CHARACTERISTIC	TEST CONDITIONS		LIMITS		UNITS
		V_{DD} (V)	TYP.	MAX.	
Propagation Delay Time: t_{PHL}, t_{PLH}		5	140	280	ns
		10	70	140	
		15	60	120	
Transition Time: t_{THL}, t_{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C_{IN}	Any Input		5	7.5	pF

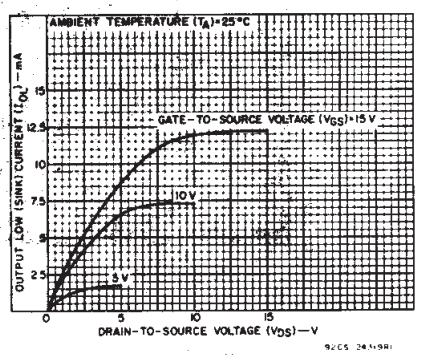


Fig.3 – Minimum output low (sink) current characteristics.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	+25 Min.	+25 Typ.	+25 Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Positive Trigger Threshold Voltage V_P Min.	–	–	5	2.2	2.2	2.2	2.2	2.2	2.9	–	V
	–	–	10	4.6	4.6	4.6	4.6	4.6	5.9	–	
	–	–	15	6.8	6.8	6.8	6.8	6.8	8.8		
V_P Max.	–	–	5	3.6	3.6	3.6	3.6	–	2.9	3.6	
	–	–	10	7.1	7.1	7.1	7.1	–	5.9	7.1	
	–	–	15	10.8	10.8	10.8	10.8	–	8.8	10.8	
Negative Trigger Threshold Voltage V_N Min.	–	–	5	0.9	0.9	0.9	0.9	0.9	1.9	–	V
	–	–	10	2.5	2.5	2.5	2.5	2.5	3.9	–	
	–	–	15	4	4	4	4	4	5.8	–	
V_N Max.	–	–	5	2.8	2.8	2.8	2.8	–	1.9	2.8	
	–	–	10	5.2	5.2	5.2	5.2	–	3.9	5.2	
	–	–	15	7.4	7.4	7.4	7.4	–	5.8	7.4	
Hysteresis Voltage V_H Min.	–	–	5	0.3	0.3	0.3	0.3	0.3	0.9	–	V
	–	–	10	1.2	1.2	1.2	1.2	1.2	2.3	–	
	–	–	15	1.6	1.6	1.6	1.6	1.6	3.5	–	
V_H Max.	–	–	5	1.6	1.6	1.6	1.6	–	0.9	1.6	
	–	–	10	3.4	3.4	3.4	3.4	–	2.3	3.4	
	–	–	15	5	5	5	5	–	3.5	5	
Output Low (Sink) Current, I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0.5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage Low-Level, V_{OL} Max.	–	5	5	0.05				–	0	0.05	V
	–	10	10	0.05				–	0	0.05	
	–	15	15	0.05				–	0	0.05	
Output Voltage High Level, V_{OH} Min.	–	0	5	4.95				4.95	5	–	
	–	0	10	9.95				9.95	10	–	
	–	0	15	14.95				14.95	15	–	
Input Current, I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

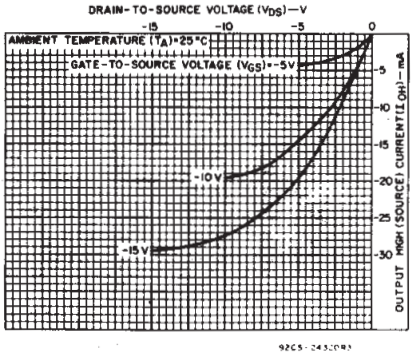


Fig.4 – Typical output high (source) current characteristics.

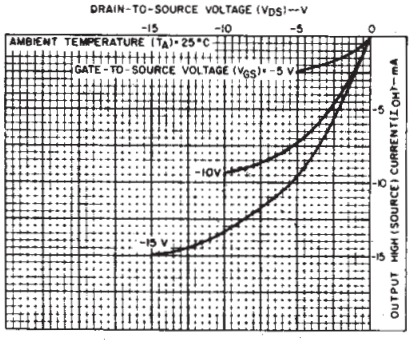


Fig.5 – Minimum output high (source) current characteristics.

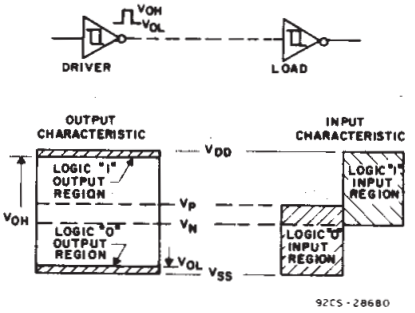
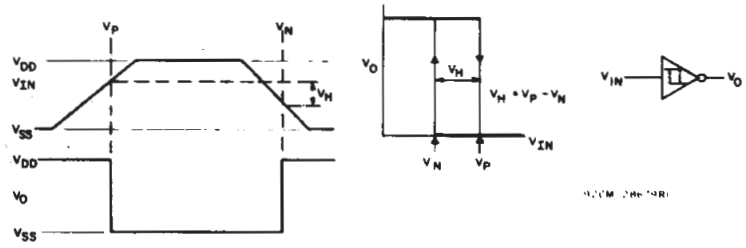


Fig.7 – Input and output characteristics.



a) Definition of V_P, V_N, V_H *b) Transfer characteristics of 1 of 6 gates*

Fig.6 – Hysteresis definition, characteristics, and test set-up.

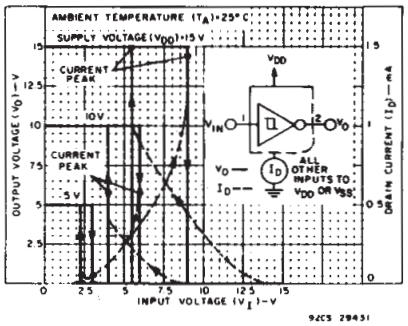


Fig.8 – Typical current and voltage transfer characteristics.

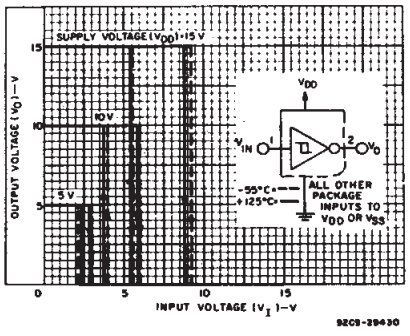


Fig.9 – Typical voltage transfer characteristics as a function of temperature.

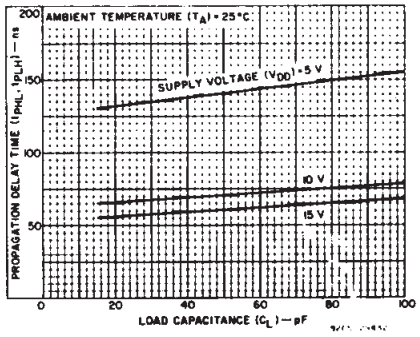


Fig.10 – Typical propagation delay time as a function of load capacitance.

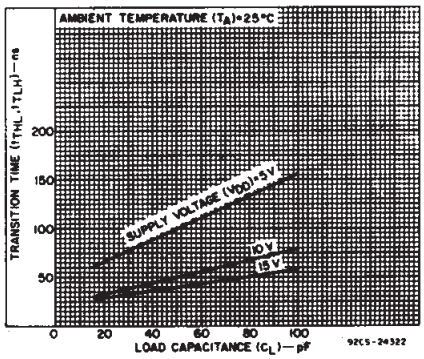


Fig.11 – Typical transition time as a function of load capacitance.

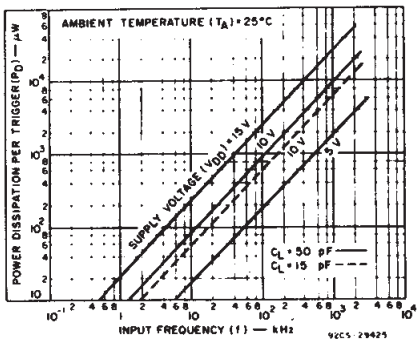


Fig.12 – Typical power dissipation per trigger as a function of input frequency.

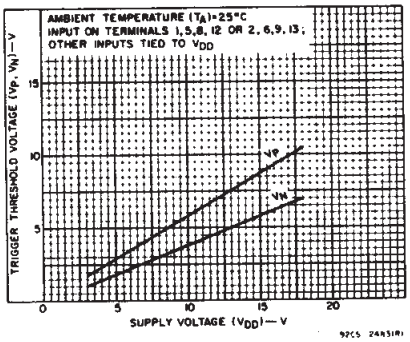


Fig.13 – Typical trigger threshold voltage as a function of supply voltage.

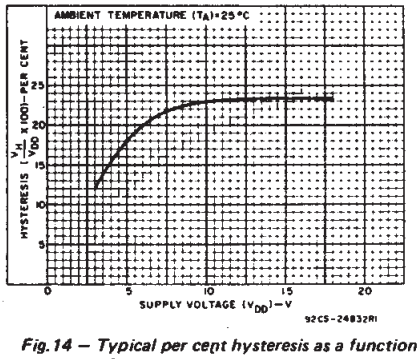


Fig.14 – Typical per cent hysteresis as a function of supply voltage.

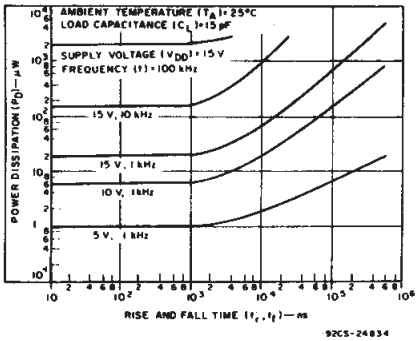


Fig.15 – Typical power dissipation as a function of rise and fall times.

APPLICATIONS

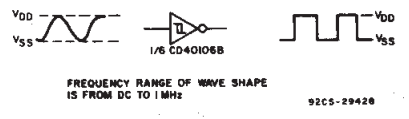


Fig.16 – Wave shaper.

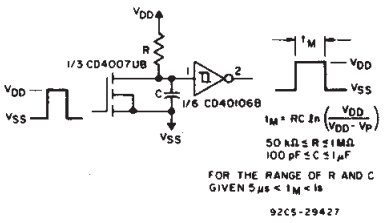


Fig.17 – Monostable multivibrator.

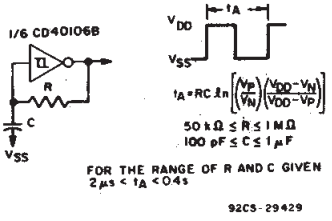


Fig.18 – Astable multivibrator.

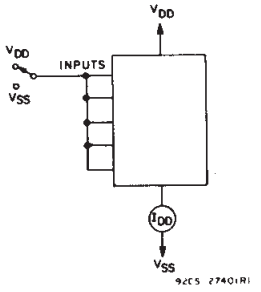


Fig.19 – Quiescent device current test circuit.

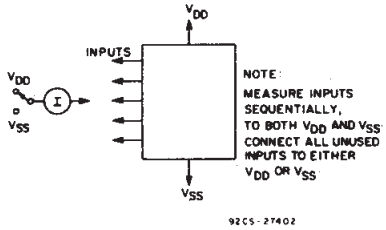


Fig.20 – Input current test circuit.

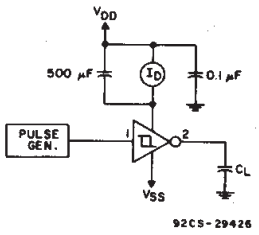
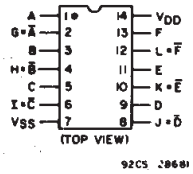
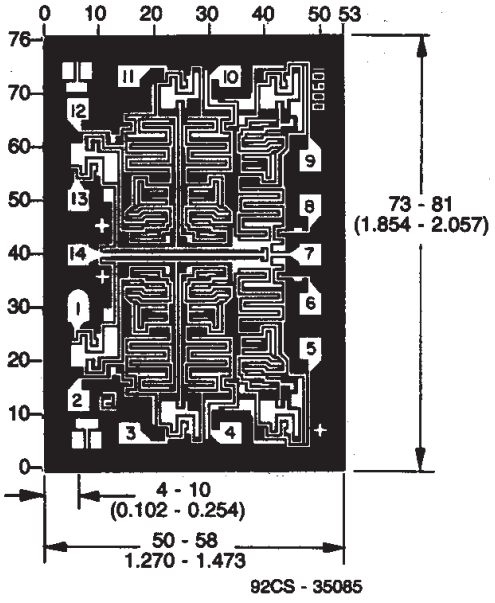


Fig.21 – Dynamic power dissipation test circuit.



TERMINAL ASSIGNMENT



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

Dimensions and Pad Layout for CD40106BH

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